



STP7NB40 STP7NB40FP

N - CHANNEL ENHANCEMENT MODE PowerMESH™ MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP7NB40	400 V	< 0.9 Ω	7.0 A
STP7NB40FP	400 V	< 0.9 Ω	4.4 A

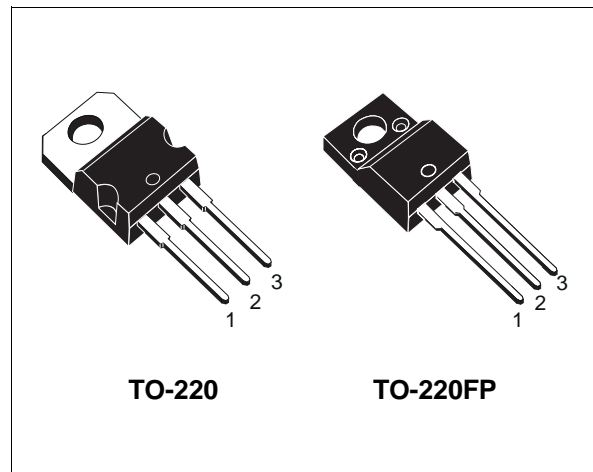
- TYPICAL R_{DS(on)} = 0.75 Ω
- EXTREMELY HIGH dV/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED

DESCRIPTION

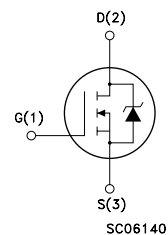
Using the latest high voltage MESH OVERLAY™ process, SGS-Thomson has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest RDS(on) per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP7NB40	STP7NB40FP	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	400		V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	400		V
V _{GS}	Gate-source Voltage	± 30		V
I _D	Drain Current (continuous) at T _c = 25 °C	7	4.4	A
I _D	Drain Current (continuous) at T _c = 100 °C	4.4	2.8	A
I _{DM} (•)	Drain Current (pulsed)	28	28	A
P _{tot}	Total Dissipation at T _c = 25 °C	100	35	W
	Derating Factor	0.8	0.28	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	4.5	4.5	V/ns
V _{ISO}	Insulation Withstand Voltage (DC)	—	2000	V
T _{stg}	Storage Temperature	-65 to 150		°C
T _j	Max. Operating Junction Temperature	150		°C

(•) Pulse width limited by safe operating area

(1) I_{SD} ≤ 7A, di/dt ≤ 200 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

This is preliminary information on a new product now in development or undergoing evaluation. Details are subject to change without notice.

STP7NB40/FP

THERMAL DATA

		TO-220	TO-220FP	
R _{thj-case}	Thermal Resistance Junction-case Max	1.25	3.57	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient Max	62.5		°C/W
R _{thc-sink}	Thermal Resistance Case-sink Typ	0.5		°C/W
T _l	Maximum Lead Temperature For Soldering Purpose	300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max, $\delta < 1\%$)	7	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	300	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μ A V _{GS} = 0	400			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _c = 125 °C			1 50	μ A μ A
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = \pm 30 V			\pm 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μ A	3	4	5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V I _D = 3.5 A		0.75	0.9	Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} x R _{DS(on)max} V _{GS} = 10 V	7			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} x R _{DS(on)max} I _D = 3.5 A	2.5	4.2		S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		705	720	pF
C _{oss}	Output Capacitance			132	175	pF
C _{rss}	Reverse Transfer Capacitance			17	25	pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 200\text{ V}$ $I_D = 3.5\text{ A}$		11.5	16	ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)		7.5	11	ns
Q_g	Total Gate Charge	$V_{DD} = 320\text{ V}$ $I_D = 7\text{ A}$ $V_{GS} = 10\text{ V}$		21	30	nC
Q_{gs}	Gate-Source Charge			7.3		nC
Q_{gd}	Gate-Drain Charge			8.5		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 320\text{ V}$ $I_D = 7\text{ A}$		9.5	15	ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		9	14	ns
t_c	Cross-over Time	(see test circuit, figure 5)		16.5	25	ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				7	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				28	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 7\text{ A}$ $V_{GS} = 0$			1.6	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 7\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		300		ns
Q_{rr}	Reverse Recovery Charge			2		μC
I_{RRM}	Reverse Recovery Current			13.7		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

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